

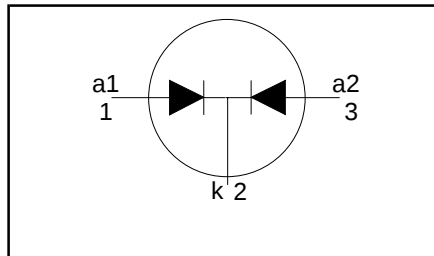
Rectifier diodes ultrafast, rugged

BYV32E, BYV32EB series

FEATURES

- Low forward volt drop
- Fast switching
- Soft recovery characteristic
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$$V_R = 150 \text{ V} / 200 \text{ V}$$

$$V_F \leq 0.85 \text{ V}$$

$$I_{O(AV)} = 20 \text{ A}$$

$$I_{RRM} = 0.2 \text{ A}$$

$$t_{rr} \leq 25 \text{ ns}$$

GENERAL DESCRIPTION

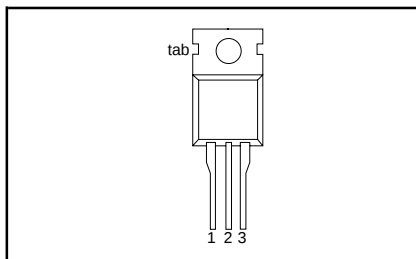
Dual, ultra-fast, epitaxial rectifier diodes intended for use as output rectifiers in high frequency switched mode power supplies.

The BYV32E series is supplied in the SOT78 conventional leaded package.
The BYV32EB series is supplied in the SOT404 surface mounting package.

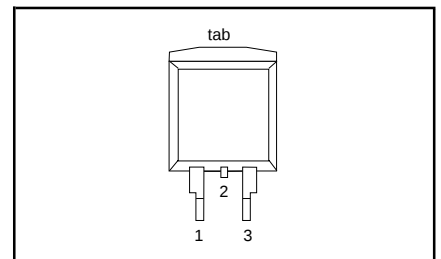
PINNING

PIN	DESCRIPTION
1	anode 1 (a)
2	cathode (k) ¹
3	anode 2 (a)
tab	cathode (k)

SOT78 (TO220AB)



SOT404



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V_{RRM}	Peak repetitive reverse voltage	BYV32E / BYV32EB square wave; $\delta = 0.5$; $T_{mb} \leq 115\text{ }^{\circ}\text{C}$ $t = 25\text{ }\mu\text{s}$; $\delta = 0.5$; $T_{mb} \leq 115\text{ }^{\circ}\text{C}$ $t = 10\text{ ms}$ $t = 8.3\text{ ms}$ sinusoidal; with reapplied $V_{RWM(max)}$ $t_p = 2\text{ }\mu\text{s}$; $\delta = 0.001$ $t_p = 100\text{ }\mu\text{s}$	-	-150 150	-200 200	V
V_{RWM}	Crest working reverse voltage		-	150	200	V
V_R	Continuous reverse voltage		-	150	200	V
$I_{O(AV)}$	Average rectified output current (both diodes conducting)		-	20		A
I_{FRM}	Repetitive peak forward current per diode		-	20		A
I_{FSM}	Non-repetitive peak forward current per diode		-	125		A
			-	137		A
I_{RRM}	Repetitive peak reverse current per diode		-	0.2		A
I_{RSM}	Non-repetitive peak reverse current per diode		-	0.2		A
T_{stg}	Storage temperature		-40	150		$^{\circ}\text{C}$
T_j	Operating junction temperature	-	150		$^{\circ}\text{C}$	

1 It is not possible to make connection to pin 2 of the SOT404 package

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ESD LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_C	Electrostatic discharge capacitor voltage	Human body model; $C = 250 \text{ pF}$; $R = 1.5 \text{ k}\Omega$	-	8	kV

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th \text{ j-mb}}$	Thermal resistance junction to mounting base	per diode	-	-	2.4	K/W
		both diodes	-	-	1.6	K/W
$R_{th \text{ j-a}}$	Thermal resistance junction to ambient	SOT78 package, in free air	-	60	-	K/W
		SOT404 and SOT428 packages, pcb mounted, minimum footprint, FR4 board	-	50	-	K/W

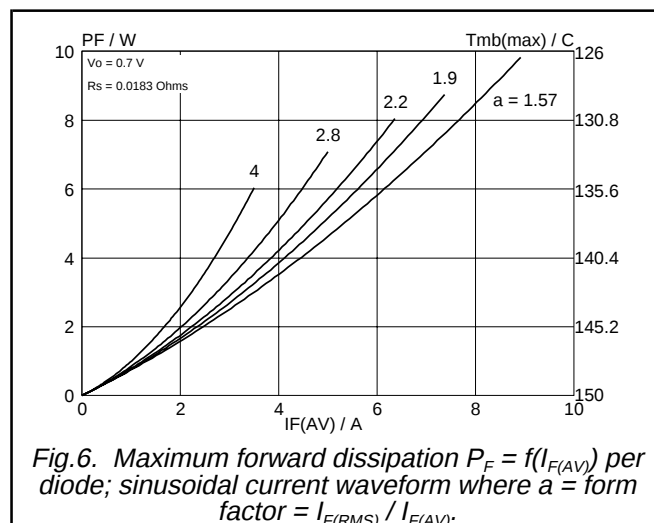
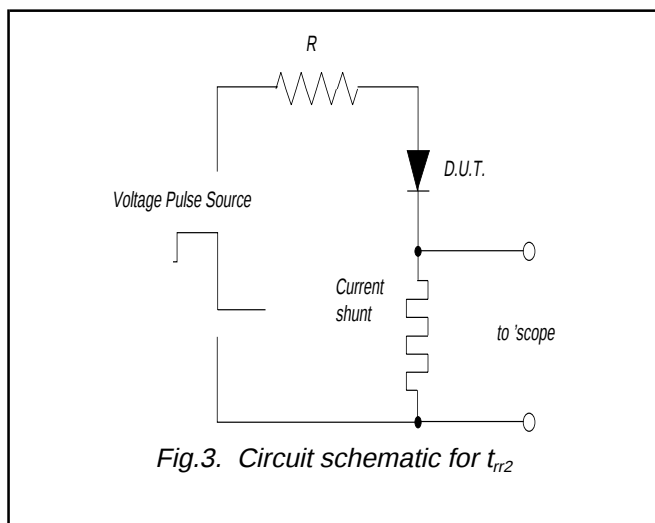
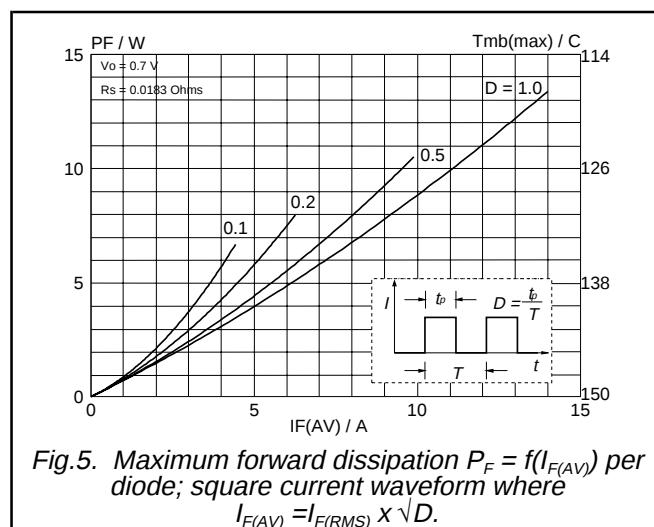
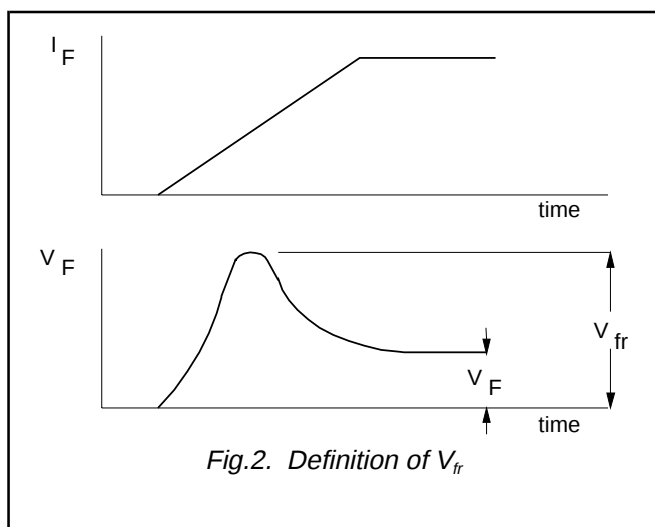
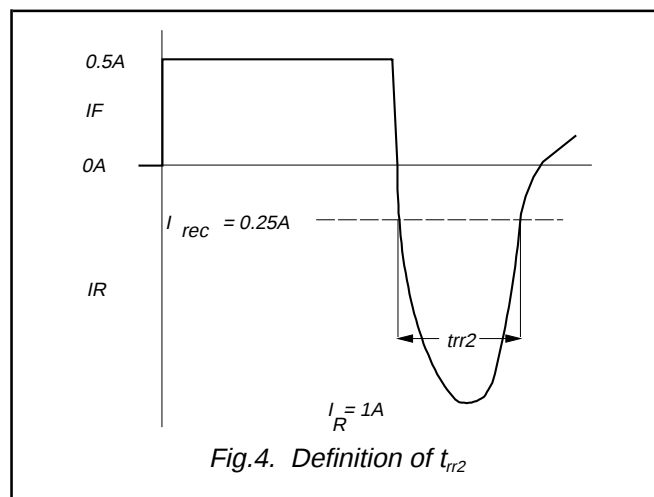
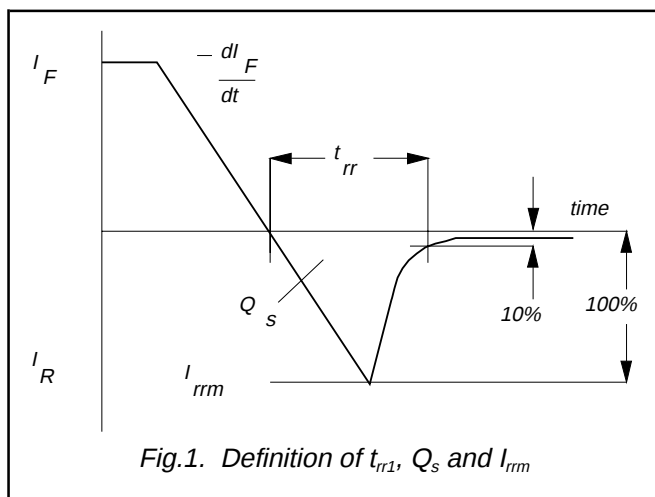
ELECTRICAL CHARACTERISTICS

characteristics are per diode at $T_j = 25^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	Forward voltage	$I_F = 8 \text{ A}$; $T_j = 150^\circ\text{C}$	-	0.72	0.85	V
		$I_F = 20 \text{ A}$	-	1.00	1.15	V
I_R	Reverse current	$V_R = V_{RWM}$; $T_j = 100^\circ\text{C}$	-	0.2	0.6	mA
		$V_R = V_{RWM}$	-	6	30	μA
Q_s	Reverse recovery charge	$I_F = 2 \text{ A}$; $V_R \geq 30 \text{ V}$; $-di_F/dt = 20 \text{ A}/\mu\text{s}$	-	8	12.5	nC
t_{rr1}	Reverse recovery time	$I_F = 1 \text{ A}$; $V_R \geq 30 \text{ V}$; $-di_F/dt = 100 \text{ A}/\mu\text{s}$	-	20	25	ns
t_{rr2}	Reverse recovery time	$I_F = 0.5 \text{ A}$ to $I_R = 1 \text{ A}$; $I_{rec} = 0.25 \text{ A}$	-	10	20	ns
V_{fr}	Forward recovery voltage	$I_F = 1 \text{ A}$; $di_F/dt = 10 \text{ A}/\mu\text{s}$	-	1	-	V

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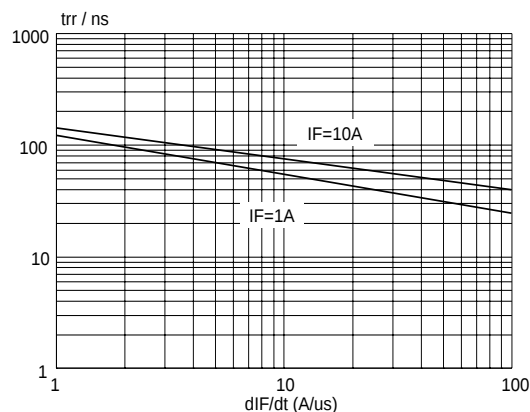


Fig.7. Maximum t_{rr} at $T_j = 25^\circ C$; per diode

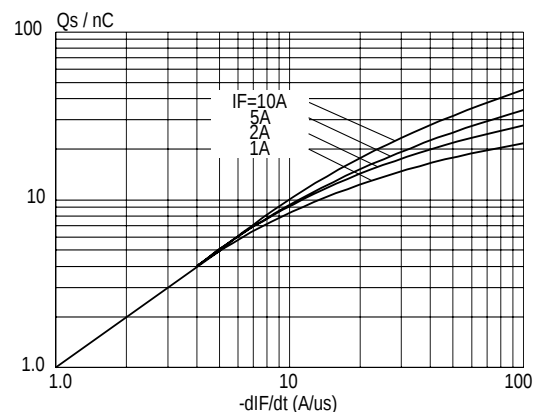


Fig.10. Maximum Q_s at $T_j = 25^\circ C$; per diode

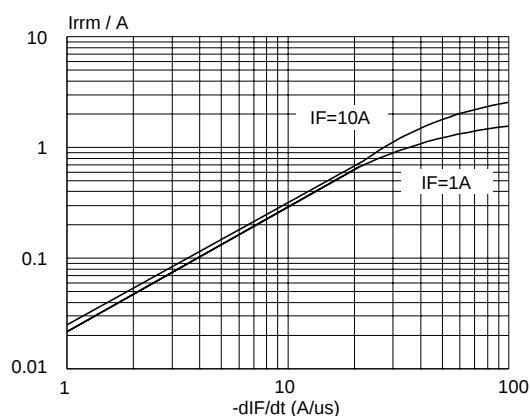


Fig.8. Maximum I_{rrm} at $T_j = 25^\circ C$; per diode

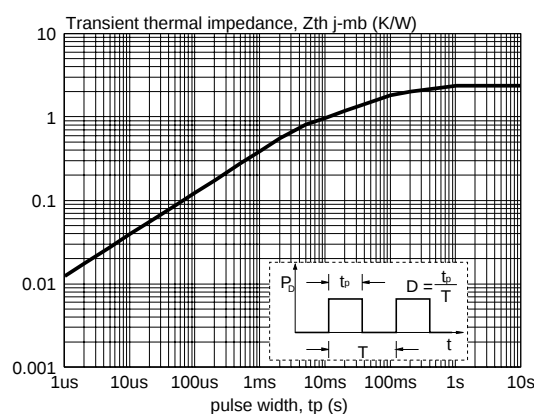


Fig.11. Transient thermal impedance; per diode;
 $Z_{th j-mb} = f(t_p)$.

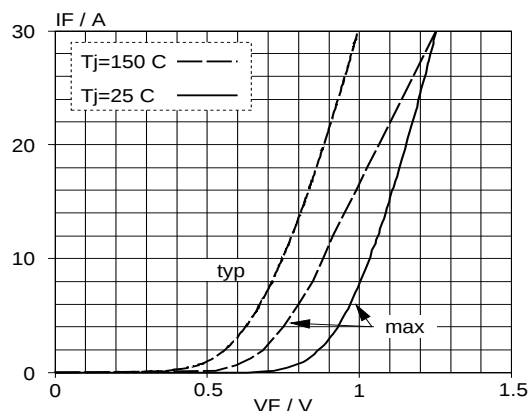


Fig.9. Typical and maximum forward characteristic per diode; $I_F = f(V_F)$; parameter T_j

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MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

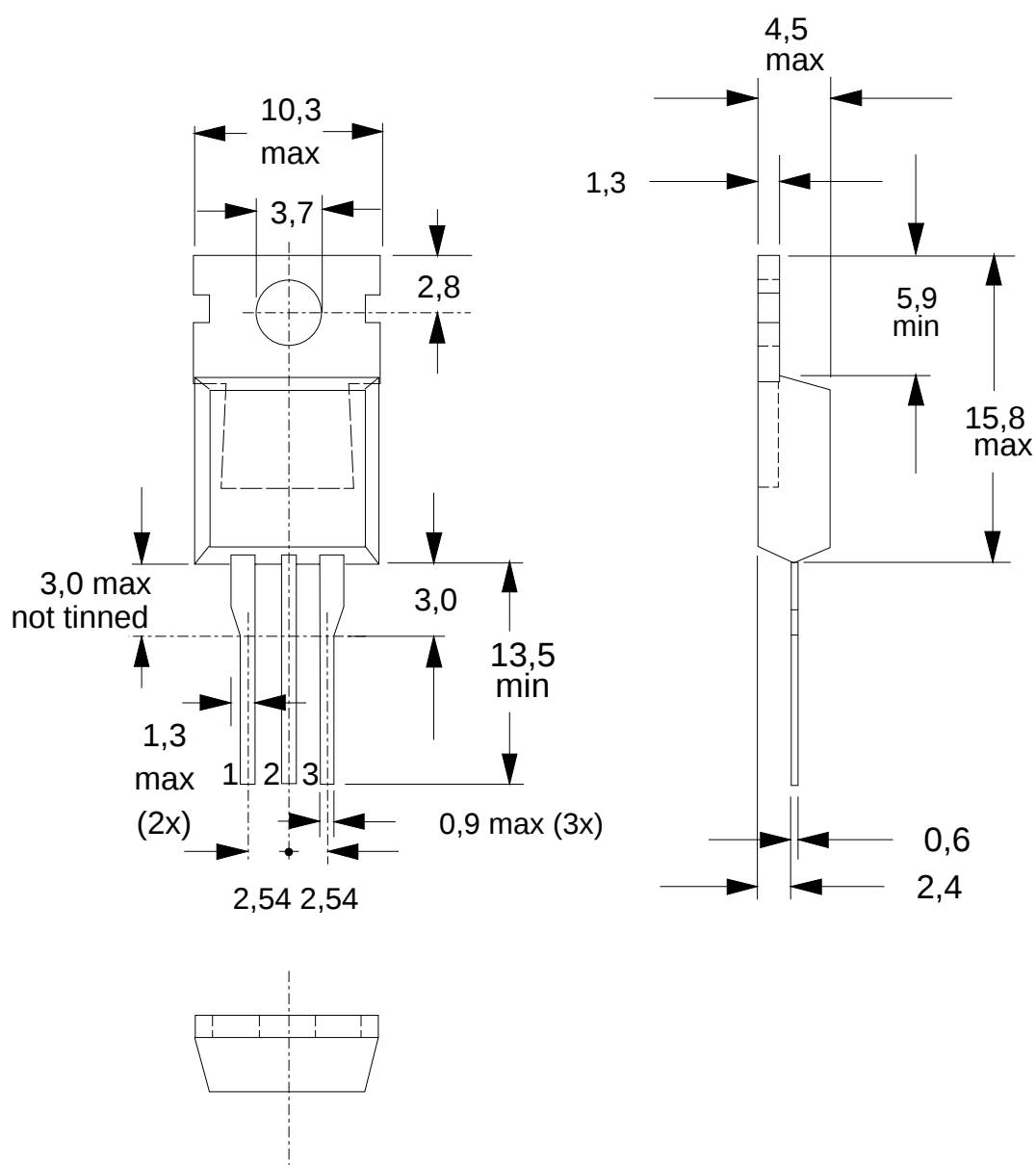


Fig.12. SOT78 (TO220AB); pin 2 connected to mounting base.

Notes

1. Refer to mounting instructions for SOT78 (TO220) envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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MECHANICAL DATA

Dimensions in mm

Net Mass: 1.4 g

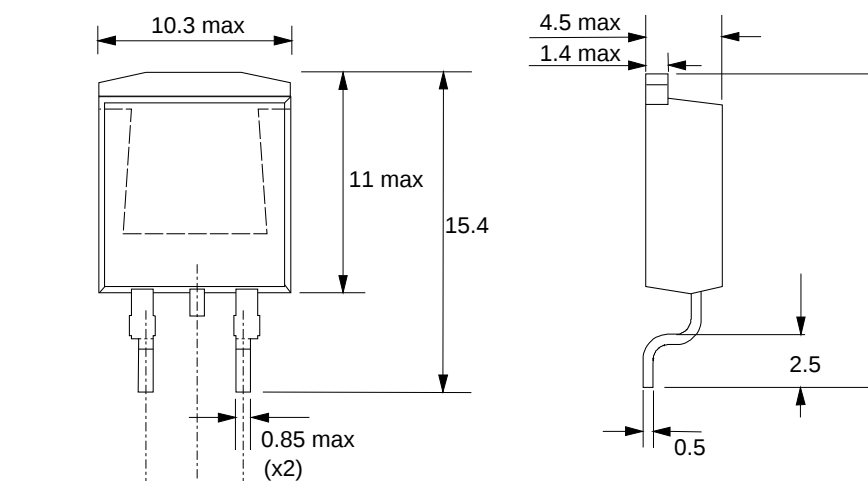


Fig.13. SOT404 : centre pin connected to mounting base.

MOUNTING INSTRUCTIONS

Dimensions in mm

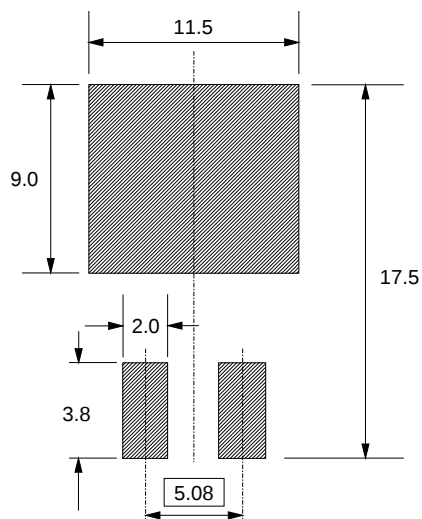


Fig.14. SOT404 : soldering pattern for surface mounting.

Notes

1. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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